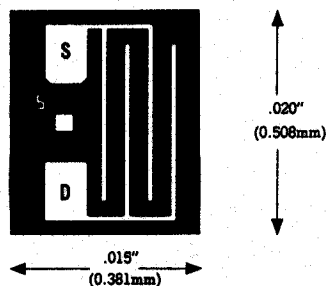


CHIP NUMBER

FN39.8



Die Size: 15 x 20 (mils)
0.381 x 0.508(mm)
3.5 x 4.5 (mils)
Pad Size: 0.089 x 0.114(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BV _{GSS}	-40	-50	-70	V	V _{DS} = 0, I _G = 1μA
I _{DSS}	0.1	3.0	10	mA	V _{DS} = 20V, V _{GS} = 0
g _{fs}	0.5	1.8	3.5	μmho	V _{DS} = 20V, V _{GS} = 0
I _{GSS}		-10	-100	pA	V _{GS} = -30V, V _{DS} = 0
r _{DS}		500	2000	Ω	V _{DS} = 100mV, V _{GS} = 0
V _{GS(off)}		-2.5	-6.0	V	V _{DS} = 20V, I _D = 1mA
C _{rss}		2.0	4.0	pF	V _{DS} = 20V, V _{GS} = 0, f = 1MHz
C _{iss}		5.0	7.0	pF	V _{DS} = 20V, V _{GS} = 0, f = 1MHz
e _n		10	30	nV/√Hz	V _{DS} = 15V, I _D = .2mA, f = 10Hz

TYPICAL DEVICE TYPES: SDF500 Thru SDF 505, 2N5515 - 2N5524, 2N4867, 2N4868

CHIP TYPE FN39.8

